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(21) International Application Number: PCT/US98/21560 (22) International Filing Date: 13 October 1998 (13.10.98) (30) Priority Data: 09/004,937 9 January 1998 (09.01.98) US (71) Applicant: ASHLAND INC. [US/US]; P.O. Box 2219, Columbus, OH 43216 (US). (72) Inventors: PETERS, Darryl, Wayne; 111 Kennedy Mill Road, Stewartville, NJ 08886 (US). WARD, Irl, E.; 1493 Amherst Court, Bethlehem, PA 18015 (US). MICHELOTTI, Frank, W.; 3560 Southwood Drive, Easton, PA 18042 (US). RIDDLE, Floyd, Jr.; 1020 Macungie Avenue, Emmaus, PA 18049 (US). (74) Agents: CONNAUGHTON, Martin; Ashland Inc., P.O.Box 2219, Columbus, OH 43216 (US) et al.		(81) Designated States: AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GE, HU, ID, IL, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, TJ, TM, TR, TT, UA, UG, UZ, VN, ARIPO patent (GH, GM, KE, LS, MW, SD, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i>
(54) Title: IMPROVEMENT IN AQUEOUS STRIPPING AND CLEANING COMPOSITIONS (57) Abstract An aqueous stripping composition comprising a mixture of an organic amine and a corrosion inhibitor which is benzotriazole alone or in combination with gallic acid, its ester or analog. The stripping composition is effective to strip photoresists, residues from plasma process generated organic, metal-organic materials, inorganic salts, oxides, hydroxides or complexes in combination with or exclusive of organic photoresist films at low temperatures with little corrosion of copper or titanium containing substrates.		